The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

- 1. (Currently Amended) A data storage device comprising:
 - a probe tip mounted on a suspension mechanism;
 - a data storage layer;

at least one conducting layer wherein a capacitance is formed between
the suspension mechanism and the at least one conducting layer <u>wherein a first</u>
<u>capacitance is formed on a first side of the suspension mechanism and a</u>
<u>second capacitance is formed on a second side of the suspension</u>
<u>mechanism</u>; and

a sensor for sensing a change in the capacitance based on a displacement of the probe tip due to the presence of a bit.

- 2. (Original) The data storage device of claim 1 wherein the data storage layer is in contact with the probe tip.
- 3. (Original) The data storage device of claim 2 wherein the data storage layer includes the bit and the bit comprises at least one of a pit or a protrusion.
- 4. (Original) The data storage device of claim 1 wherein the data storage layer comprises a polymer material.

- 5. (Previously Amended) The data storage device of claim 1 wherein the at least one conducting layer comprises a conducting thin film.
- 6. (Original) The data storage device of claim 5 wherein the conducting thin film comprises at least one of a deposited metal film of Mo, Cu, TA.
- 7. (Original) The data storage device of claim 1 wherein the conducting layer comprises a conducting substrate.
- 8. (Original) The data storage device of claim 7 wherein the conducting substrate comprises a doped silicon material.
- 9. (Original) The data storage device of claim 1 wherein the suspension mechanism includes a flexible cantilever.
- 10. (Original) The data storage device of claim 9 wherein the capacitance is formed on at least one side of the flexible cantilever.
- 11. Please cancel claim 11.
- 12. (Original) The data storage device of claim 11 wherein the change in capacitance comprises a difference in capacitance between the first capacitance and the second capacitance.

13. (Currently Amended) A method of reading data from a data storage device comprising:

suspending a probe tip over a data storage layer via a suspension mechanism;

providing at least one conducting layer wherein a capacitance is formed between the suspension mechanism and the at least one conducting layer wherein a first capacitance is formed on a first side of the suspension mechanism and a second capacitance is formed on a second side of the suspension mechanism; and

reading data from the storage device by sensing a change in the capacitance based on a displacement of the probe tip due to the presence of a bit.

- 14. (Original) The method of claim 13 wherein the data storage layer comprises a polymer material.
- 15. (Original) The method of claim 13 wherein the at least one conducting layer comprises a conducting thin film.
- 16. (Currently Amended) The method of claim 15 wherein the conducting thin film comprises at least one of a deposited metal film of Mo, Cu, TA, and an alloy.

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- 17. (Original) The method of claim 13 wherein the at least one conducting layer comprises a conducting substrate.
- 18. (Original) The method of claim 17 wherein the conducting substrate comprises a doped silicon material.
- 19. (Original) The method of claim 13 wherein the suspension mechanism further includes a flexible cantilever and the act of providing at least one conducting layer further comprises providing a conducting layer within the suspension mechanism whereby a capacitance is formed between the conducting layer and the flexible cantilever.
- 20. Please cancel claim 20.
- 21. (Original) The method of claim 20 wherein the act of sensing a change in capacitance comprises sensing a difference in capacitance between the first and second capacitance.
- 22. (Original) The method of claim 13 wherein the data storage layer includes the bit and the bit comprises at least one of a pit or protrusion.
- 23. (Original) A computer system comprising:
 - a central processing unit; and

a data storage device coupled to the central processing unit comprising:

a probe tip mounted on a suspension mechanism;

a data storage layer;

at least one conducting layer wherein a capacitance is formed between the suspension mechanism and the at least one conducting layer; and a sensor for sensing a change in the capacitance based on a

displacement of the probe tip due to the presence of a bit.

24. (Previously Amended) A data storage device comprising:

a probe tip mounted on a flexible suspension mechanism;

at least one capacitor coupled to the flexible suspension mechanism; and

a sensor for sensing a change in capacitance of the at least one capacitor

based on a displacement of the probe tip due to the presence of a bit.